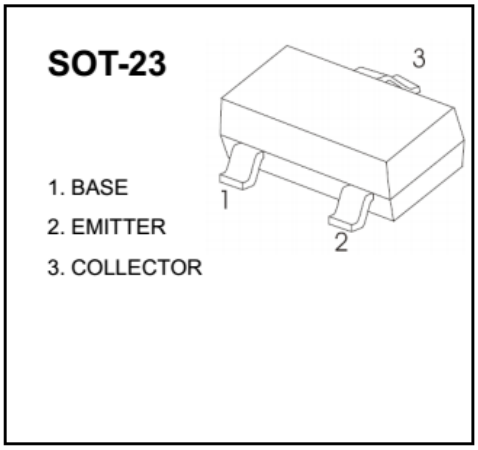
isc Silicon NPN Power Transistor SS8050



DESCRIPTION

- Low Saturation Voltage-
  : $V_{CE(sat)}$= 0.5V(Max)@ I_C =0.8A

APPLICATIONS

- Designed for high-speed switching and Amplifier applications.

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	40	V
V_{CEO}	Collector-Emitter Voltage	25	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current-Continuous	1.5	A
P_C	Collector Power Dissipation @T_C=25℃	300	mW
T_J	Junction Temperature	150	℃
T_{stg}	Storage Temperature	-55~150	℃

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
$V_{(BR)CBO}$	Collector-base breakdown voltage	I_C=100μA, I_E=0	40		V
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	I_C=0.1mA , I_B=0	25		V
$V_{(BR)EBO}$	Emitter-base breakdown voltage	I_E= 100μA, I_C=0	5		V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C=800mA; I_B= 80mA		0.5	V
$V_{BE(sat)}$	base-emitter saturation voltage	I_C= 800mA; I_B=80mA		1.2	V
I_{CBO}	collector cut-off current	V_{CB} =40 V,I_E = 0		0.1	uA
I_{CEO}	collector cut-off current	V_{CE}= 20V, I_B=0		0.1	uA
I_{EBO}	Emitter Cutoff Current	V_{EB}=5V; I_C=0		0.1	uA
h_{FE-1}	DC Current Gain	I_C= 0.1A ; V_{CE}= 1V	120	400	
h_{FE-2}	DC Current Gain	I_C=0.8A ; V_{CE}= 1V	40		
f_T	Transition frequency	V_{CE}=10V, I_C= 50mA，f=30MHz	100		MHz

Classification of h_{FE-1}

Rank	L	H	J
Range	120-200	200-350	300-400